

# HiPerFET™ Power MOSFETs Q-Class

IXFH 58N20Q  
IXFT 58N20Q

$$\begin{aligned} V_{DSS} &= 200 \text{ V} \\ I_{D25} &= 58 \text{ A} \\ R_{DS(on)} &= 40 \text{ m}\Omega \end{aligned}$$

$$t_{rr} \leq 200 \text{ ns}$$

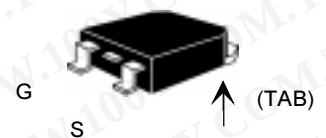
N-Channel Enhancement Mode  
Avalanche Rated High dv/dt, Low  $Q_g$

Preliminary data sheet

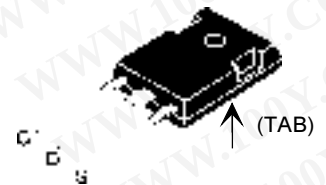


| Symbol    | Test Conditions                                                                                                                         | Maximum Ratings |                  |
|-----------|-----------------------------------------------------------------------------------------------------------------------------------------|-----------------|------------------|
| $V_{DSS}$ | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$                                                                                         | 200             | V                |
| $V_{DGR}$ | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$                                                          | 200             | V                |
| $V_{GS}$  | Continuous                                                                                                                              | $\pm 20$        | V                |
| $V_{GSM}$ | Transient                                                                                                                               | $\pm 30$        | V                |
| $I_{D25}$ | $T_C = 25^\circ\text{C}$                                                                                                                | 58              | A                |
| $I_{DM}$  | $T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$                                                                              | 232             | A                |
| $I_{AR}$  | $T_C = 25^\circ\text{C}$                                                                                                                | 58              | A                |
| $E_{AR}$  | $T_C = 25^\circ\text{C}$                                                                                                                | 30              | mJ               |
| $E_{AS}$  | $T_C = 25^\circ\text{C}$                                                                                                                | 1.0             | J                |
| dv/dt     | $I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ ,<br>$T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$ | 5               | V/ns             |
| $P_D$     | $T_C = 25^\circ\text{C}$                                                                                                                | 300             | W                |
| $T_J$     |                                                                                                                                         | -55 ... +150    | $^\circ\text{C}$ |
| $T_{JM}$  |                                                                                                                                         | 150             | $^\circ\text{C}$ |
| $T_{stg}$ |                                                                                                                                         | -55 ... +150    | $^\circ\text{C}$ |
| $T_L$     | 1.6 mm (0.062 in.) from case for 10 s                                                                                                   | 300             | $^\circ\text{C}$ |
| $M_d$     | Mounting torque                                                                                                                         | 1.13/10         | Nm/lb.in.        |
| Weight    | TO-247                                                                                                                                  | 6               | g                |
|           | TO-268                                                                                                                                  | 4               | g                |

TO-268 (D3) (IXFT) Case Style



TO-247 AD



G = Gate      D = Drain  
S = Source      TAB = Drain

## Features

- IXYS advanced low  $Q_g$  process
- International standard packages
- Low gate charge and capacitance
  - easier to drive
  - faster switching
- Low  $R_{DS(on)}$
- Unclamped Inductive Switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

## Advantages

- Easy to mount
- Space savings
- High power density

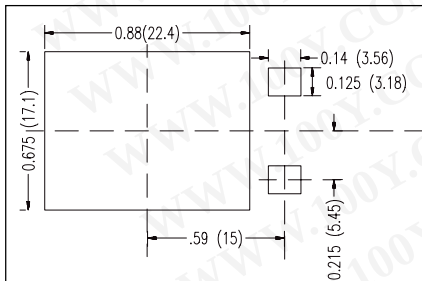
| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified)                                     | Characteristic Values |      |                      |
|--------------|-----------------------------------------------------------------------------------------------------------------|-----------------------|------|----------------------|
|              |                                                                                                                 | Min.                  | Typ. | Max.                 |
| $V_{DSS}$    | $V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$                                                                | 200                   |      | V                    |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$                                                                        | 2.0                   |      | V                    |
| $I_{GSS}$    | $V_{GS} = \pm 20 \text{ V}_{DC}$ , $V_{DS} = 0$                                                                 |                       |      | $\pm 100 \text{ nA}$ |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $T_J = 25^\circ\text{C}$                                                                   |                       |      | 25 $\mu\text{A}$     |
|              | $V_{GS} = 0 \text{ V}$ , $T_J = 125^\circ\text{C}$                                                              |                       |      | 1 mA                 |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$<br>Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2\%$ |                       |      | 40 m $\Omega$        |

| Symbol                    | Test Conditions                                                                                                                             | Characteristic Values<br>(T <sub>J</sub> = 25°C, unless otherwise specified) |      |      |    |
|---------------------------|---------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------|------|------|----|
|                           |                                                                                                                                             | Min.                                                                         | Typ. | Max. |    |
| <b>g<sub>fs</sub></b>     | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 0.5 I <sub>D25</sub> , pulse test                                                                  | 24                                                                           | 34   |      | S  |
| <b>C<sub>iss</sub></b>    | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz                                                                                    |                                                                              | 3600 |      | pF |
| <b>C<sub>oss</sub></b>    |                                                                                                                                             |                                                                              | 870  |      | pF |
| <b>C<sub>rss</sub></b>    |                                                                                                                                             |                                                                              | 280  |      | pF |
| <b>t<sub>d(on)</sub></b>  | V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> , I <sub>D</sub> = 0.5 I <sub>D25</sub><br>R <sub>G</sub> = 1.5 Ω (External) |                                                                              | 20   |      | ns |
| <b>t<sub>r</sub></b>      |                                                                                                                                             |                                                                              | 40   |      | ns |
| <b>t<sub>d(off)</sub></b> |                                                                                                                                             |                                                                              | 40   |      | ns |
| <b>t<sub>f</sub></b>      |                                                                                                                                             |                                                                              | 13   |      | ns |
| <b>Q<sub>g(on)</sub></b>  | V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> , I <sub>D</sub> = 0.5 I <sub>D25</sub>                                      |                                                                              | 98   | 140  | nC |
| <b>Q<sub>gs</sub></b>     |                                                                                                                                             |                                                                              | 25   | 35   | nC |
| <b>Q<sub>gd</sub></b>     |                                                                                                                                             |                                                                              | 45   | 70   | nC |
| <b>R<sub>thJC</sub></b>   |                                                                                                                                             |                                                                              |      | 0.42 | KW |
| <b>R<sub>thCK</sub></b>   | (TO-247)                                                                                                                                    |                                                                              | 0.25 |      | KW |

## Source-Drain Diode

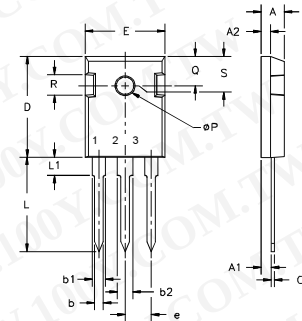
| Symbol                | Test Conditions                                                                                        | Characteristic Values<br>(T <sub>J</sub> = 25°C, unless otherwise specified) |      |      |    |
|-----------------------|--------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------|------|------|----|
|                       |                                                                                                        | min.                                                                         | typ. | max. |    |
| <b>I<sub>S</sub></b>  | V <sub>GS</sub> = 0 V                                                                                  |                                                                              |      | 58   | A  |
| <b>I<sub>SM</sub></b> | Repetitive;                                                                                            |                                                                              |      | 232  | A  |
| <b>V<sub>SD</sub></b> | I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V,<br>Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 % |                                                                              |      | 1.5  | V  |
| <b>t<sub>rr</sub></b> | I <sub>F</sub> = I <sub>S</sub> -di/dt = 100 A/μs, V <sub>R</sub> = 100 V                              |                                                                              | 0.7  | 200  | ns |
| <b>Q<sub>RM</sub></b> |                                                                                                        |                                                                              | 7    |      | μC |
| <b>I<sub>RM</sub></b> |                                                                                                        |                                                                              |      |      | A  |

## Min. Recommended Footprint Dimensions in mm and inches



勝特力材料 886-3-5753170  
勝特力电子(上海) 86-21-34970699  
勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

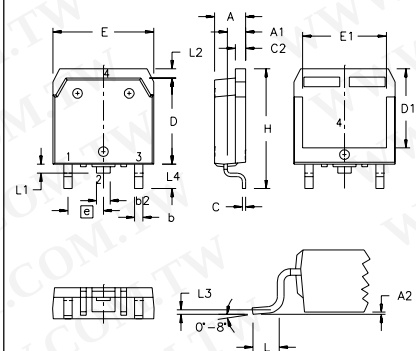
## TO-247 AD Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

| Dim.           | Millimeter |       | Inches   |       |
|----------------|------------|-------|----------|-------|
|                | Min.       | Max.  | Min.     | Max.  |
| A              | 4.7        | 5.3   | .185     | .209  |
| A <sub>1</sub> | 2.2        | 2.54  | .087     | .102  |
| A <sub>2</sub> | 2.2        | 2.6   | .059     | .098  |
| b              | 1.0        | 1.4   | .040     | .055  |
| b <sub>1</sub> | 1.65       | 2.13  | .065     | .084  |
| b <sub>2</sub> | 2.87       | 3.12  | .113     | .123  |
| C              | .4         | .8    | .016     | .031  |
| D              | 20.80      | 21.46 | .819     | .845  |
| E              | 15.75      | 16.26 | .610     | .640  |
| e              | 5.20       | 5.72  | 0.205    | 0.225 |
| L              | 19.81      | 20.32 | .780     | .800  |
| L <sub>1</sub> |            | 4.50  |          | .177  |
| ØP             | 3.55       | 3.65  | .140     | .144  |
| Q              | 5.89       | 6.40  | 0.232    | 0.252 |
| R              | 4.32       | 5.49  | .170     | .216  |
| S              | 6.15 BSC   |       | .242 BSC |       |

## TO-268 Outline



| SYM            | INCHES   |      | MILLIMETERS |       |
|----------------|----------|------|-------------|-------|
|                | MIN      | MAX  | MIN         | MAX   |
| A              | .193     | .201 | 4.90        | 5.10  |
| A <sub>1</sub> | .106     | .114 | 2.70        | 2.90  |
| A <sub>2</sub> | .001     | .010 | 0.02        | 0.25  |
| b              | .045     | .057 | 1.15        | 1.45  |
| b <sub>2</sub> | .075     | .083 | 1.90        | 2.10  |
| C              | .016     | .026 | 0.40        | 0.65  |
| C <sub>2</sub> | .057     | .063 | 1.45        | 1.60  |
| D              | .543     | .551 | 13.80       | 14.00 |
| D <sub>1</sub> | .488     | .500 | 12.40       | 12.70 |
| E              | .624     | .632 | 15.85       | 16.05 |
| E <sub>1</sub> | .524     | .535 | 13.30       | 13.60 |
| e              | .215 BSC |      | 5.45 BSC    |       |
| H              | .736     | .752 | 18.70       | 19.10 |
| L              | .094     | .106 | 2.40        | 2.70  |
| L <sub>1</sub> | .047     | .055 | 1.20        | 1.40  |
| L <sub>2</sub> | .039     | .045 | 1.00        | 1.15  |
| L <sub>3</sub> | .010 BSC |      | 0.25 BSC    |       |
| L <sub>4</sub> | .150     | .161 | 3.80        | 4.10  |

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025